TOSHIBA Transistor Silicon NPN Epitaxial Type

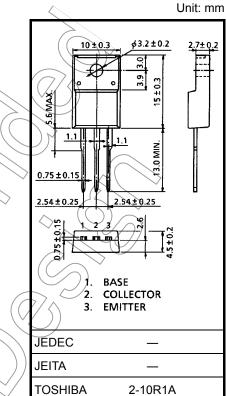
# 2SC4881

#### **High-Current Switching Applications**

- Low saturation voltage: VCE (sat) = 0.4 V (max)
- High-speed switching:  $t_{stg} = 0.8 \ \mu s \ (typ.)$

## Absolute Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V <sub>CBO</sub>	60	V
Collector-emitter voltage		V <sub>CEO</sub>	50	$(\mathcal{N} \land)$
Emitter-base voltage		V <sub>EBO</sub>	5	V V
Collector current	DC	Ι <sub>C</sub>	5	$\searrow$
	Pulse	I <sub>CP</sub>	8	
Base current		Ι <sub>Β</sub>		A
Collector power dissipation	Ta = 25°C	Pc	2.0	W
	Tc = 25°C	FC (	20	VV
Junction temperature		Tj	150	<-c
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

Weight: 1.7 g (typ.)

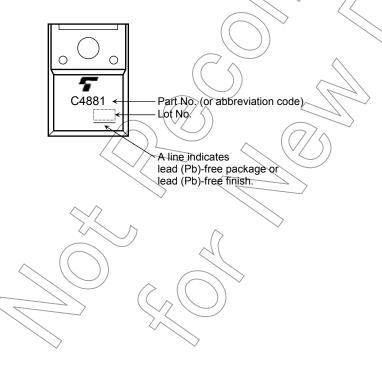
reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

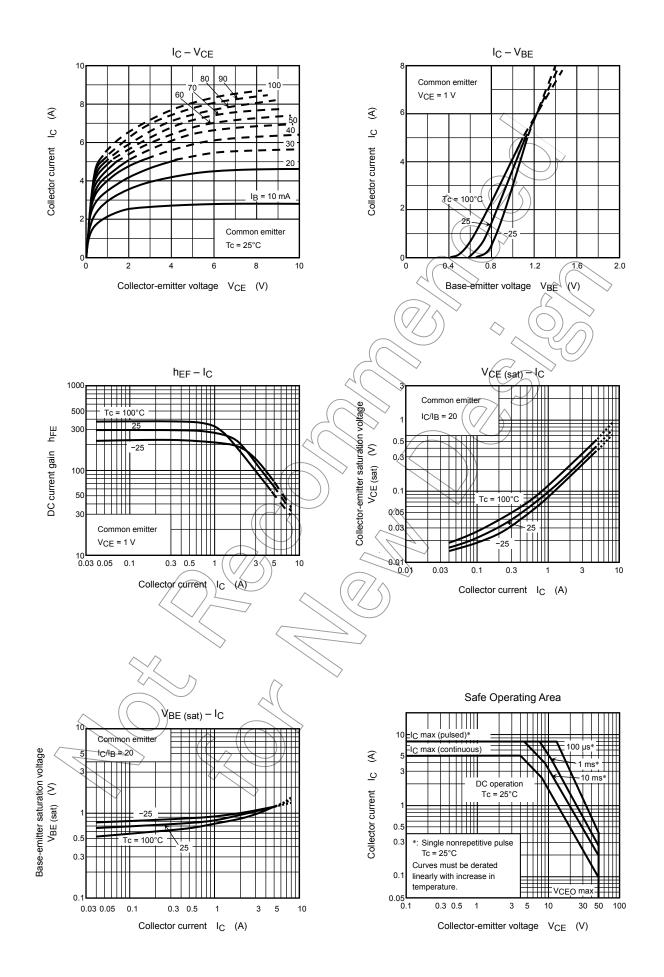
Electrical Characteristics (Tc = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	current	I <sub>CBO</sub>	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0	_	—	1	μA
Emitter cut-off cu	rrent	I <sub>EBO</sub>	V <sub>EB</sub> = 6 V, I <sub>C</sub> = 0	_	_	1	μA
Collector-emitter	breakdown voltage	V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	50	_	_	V
DC current gain		h <sub>FE (1)</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 1 A	100	_	320	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 2.5 A	60	-7(	_	
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 2.5 A, I <sub>B</sub> = 125 mA		0.25	0.4	V
Base-emitter satu	ration voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = 2.5 A, I <sub>B</sub> = 125 mA	$\bigcirc$	1.0	1.3	V
Transition freque	ncy	f <sub>T</sub>	V <sub>CB</sub> = 4 V, I <sub>C</sub> = 1 A		100	_	MHz
Collector output of	capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	45		pF
Switching time	Turn-on time	t <sub>on</sub>	20 µs Input	_ (	0.1	$\checkmark$	
	Storage time	t <sub>stg</sub>			0.8	) –	μs
	Fall time	t <sub>f</sub>	$V_{CC} = 30 V$ $I_{B1} = -I_{B2} = 125 \text{ mA, duty cycle} \le 1\%$	$\langle \mathcal{O} \rangle$	0.1	_	

# Marking



# **TOSHIBA**



### **RESTRICTIONS ON PRODUCT USE**

Handbook" etc.

The information contained herein is subject to change without notice.

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